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rinsing the substrate with an aqueous medium comprising an anti-corrosive agent including an organic acid selected from the group consisting of mono- and polycarboxylic acids in an amount effective to minimize metal corrosion.

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83. (AMENDED) A method according to claim 80 in which the organic carboxylic acid includes a mono-carboxylic acid.

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88. (AMENDED) A method for rinsing metallized semiconductor substrates containing copper following treatment of the substrates with an etch residue removal chemistry, the method comprising the steps of:

providing at least one semiconductor substrate having copper thereon, the substrate further having etch residue removal chemistry thereon; and

rinsing the substrate with an aqueous medium comprising an amount of acetic acid effective to minimize metal corrosion of the copper.

89. (AMENDED) A method for rinsing metallized semiconductor substrates containing titanium nitride following treatment of the substrates with an etch residue removal chemistry, the method comprising the steps of:

providing at least one semiconductor substrate having titanium nitride thereon, the substrate further having etch residue removal chemistry thereon; and

rinsing the substrate with an aqueous medium comprising an amount of acetic acid effective to minimize metal corrosion of the titanium nitride.

90. (AMENDED) A method for rinsing metallized semiconductor substrates following treatment of the substrates with an etch residue removal chemistry, comprising:

providing at least one metallized semiconductor substrate, the substrate having etch residue removal chemistry thereon;

contacting the substrate with an aqueous medium containing one or more anti-corrosive chemical agents wherein the concentration of the anti-corrosive chemical agent or agents is maintained at a controlled level or within a predetermined range, and the

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substrate in maintained in contact with the chemical agent or agents for a predetermined time.

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98. (AMENDED) A method for rinsing metallized semiconductor substrates following treatment of the substrates with an etch residue removal chemistry, comprising:

providing at least one metallized semiconductor substrate, the substrate having etch residue removal chemistry thereon;

contacting the substrate with an aqueous rinse medium containing anti-corrosive chemical agent including an organic compound, wherein the amount of the anti-corrosive chemical agent in the aqueous medium is maintained in a controlled manner, at a predetermined concentration or within a predetermined range, conducting the contacting step for a predetermined time, and

then rinsing the substrate with deionized water substantially free of the anti-corrosive chemical agent.

Please add new Claims 112 – 121:

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--112. (NEW) The method according to claim 80 wherein the etch residue removal chemistry includes N-methylpyrrolidinone.

113. (NEW) The method according to claim 80 wherein the etch residue removal chemistry includes hydroxylamine.

~~114.~~ (NEW) The method according to claim 80 wherein the aqueous solution consists essentially of a mono-carboxylic acid and water.

~~115.~~ (NEW) The method according to claim 114 wherein the wherein the aqueous solution consists essentially of acetic acid and water.

116. (NEW) The method of claim 80 wherein the rinsing step includes positioning the substrate with etch residue removal chemistry thereon into a rinse vessel and introducing the aqueous medium into the rinse vessel.

117. (NEW) The method of claim 90 wherein the contacting step includes positioning the substrate with etch residue removal chemistry thereon into a rinse vessel and introducing the aqueous medium into the rinse vessel.

118. (NEW) The method of claim 98 wherein the contacting step includes positioning the substrate with etch residue removal chemistry thereon into a rinse vessel and introducing the aqueous medium into the rinse vessel.

119. (NEW) The method of claim 80 wherein the rinsing step minimizes corrosion of metal on the metallized substrate and rinses the etch residue removal chemistry from the substrate.

120. (NEW) The method of claim 90 wherein the contacting step minimizes corrosion of metal on the metallized substrate and rinses the etch residue removal chemistry from the substrate.

121. (NEW) The method of claim 98 wherein the contacting step minimizes corrosion of metal on the metallized substrate and rinses the etch residue removal chemistry from the substrate.--

REMARKS

Claims 80, 83, 88, 89, 90 and 98 have been amended. Claims 112 – 121 are new. Claims 80 – 121 are pending. A marked up copy of the amended claims is provided as Attachment A.